SWITCHMODE Series NPN Silicon Power Transistor

- ... designed for high speed, high current, high power applications.
- · Very fast switching times: TF max. = $0.4 \mu s$ at IC = 8 A

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO(sus)	200	Vdc
Collector–Base Voltage	VCBO	250	Vdc
Emitter-Base Voltage	V _{EBO}	7	Vdc
Collector–Emitter Voltage (V _{BE} = −2.5 V)	V _{CEX}	250	Vdc
Collector–Emitter Voltage ($R_{BE} = 100 \Omega$)	VCER	240	Vdc
Collector–Current — Continuous — Peak (pw ≤ 10 ms)	I _C	15 20	Adc Apk
Base-Current continuous	ΙΒ	3	Adc
Total Power Dissipation @ T _C = 25°C	P _D	120	Watts
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to 200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θJC	1.46	°C/W

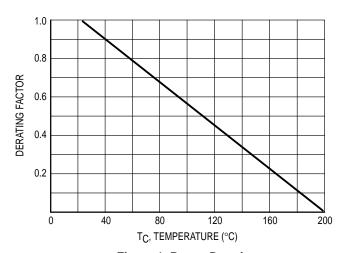


Figure 1. Power Derating

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BUX41

15 AMPERES **NPN SILICON POWER METAL TRANSISTOR 200 VOLTS 120 WATTS**



CASE 1-07 TO-204AA (TO-3)



BUX41

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

	Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS ¹				•	•
Collector–Emitter Sustainir (I _C = 200 mA, I _B = 0, L =		VCEO(sus)	200		Vdc
Collector Cutoff Current at (V _{CE} = 250 V, V _{BE} = -1 (V _{CE} = 250 V, V _{BE} = -1	.5 V)	ICEX		1.0 5.0	mAdc
Collector–Emitter Cutoff Co (V _{CE} = 160 V)	urrent	ICEO		1.0	mAdc
Emitter-Base Reverse Volt (I _E = 50 mA)	age	VEBO	7		V
Emitter–Cutoff Current (V _{EB} = 5 V)		IEBO		1.0	mAdc
SECOND BREAKDOWN				•	
Second Breakdown Collect (V _{CE} = 30 V, t = 1 s) (V _{CE} = 135 V, t = 1 s)	tor Current with base forward biased	I _{S/b}	4.0 0.15		Adc
ON CHARACTERISTICS ¹		•			•
DC Current Gain (I _C = 5 A, V _{CE} = 4 V) (I _C = 8 A. V _{CE} = 4 V)		hFE	15 8	45	
Collector–Emitter Saturation (I _C = 5 A, I _B = 0.5 A) (I _C = 8 A, I _B = 1 A)	on Voltage	VCE(sat)		1.2 1.6	Vdc
Base–Emitter Saturation V (I _C = 8 A, I _B = 1 A)	oltage	V _{BE} (sat)		2.0	Vdc
DYNAMIC CHARACTERIST	rics	•			
Current Gain — Bandwidth (V _{CE} = 15 V, I _C = 1 A, f		fΤ	8.0		MHz
SWITCHING CHARACTERI	STICS (Resistive Load)	<u>.</u>		•	-
Turn-on Time		ton		0.6	μs
Storage Time	$(I_C = 8 \text{ A}, I_{B1} = I_{B2} = 1 \text{ A},$ $V_{CC} = 150 \text{ V}, R_C = 18.75 \Omega)$	t _S		1.5	
Fall Time		t _f		0.4	1

¹ Pulse Test: Pulse Width $\leq 300 \,\mu\text{s}$, Duty Cycle $\leq 2\%$.

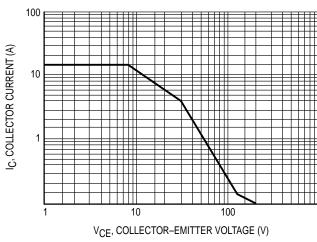
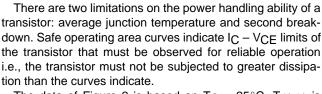


Figure 2. Active Region Safe Operating Area



The data of Figure 2 is based on $T_C = 25^{\circ}C$, $T_{J(pk)}$ is variable depending on power level. Second breakdown limitations do not derate the same as thermal limitations.

At high case temperatures, thermal limitations will reduce the power that can handled to values less than the limitations imposed by second breakdown.

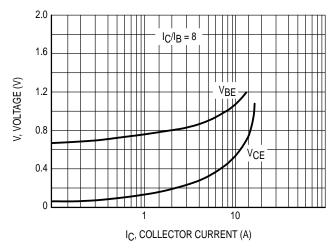
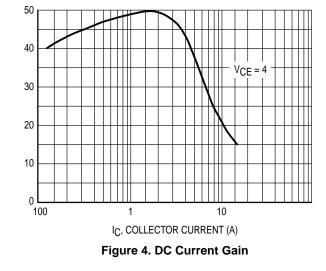


Figure 3. "On" Voltages



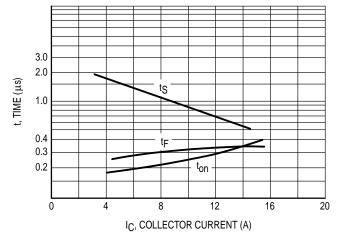
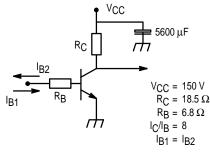


Figure 5. Resistive Switching Performance



R_C - R_B: Non inductive resistances

Figure 6. Switching Times Test Circuit

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